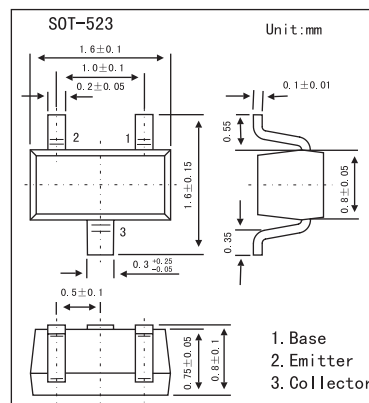


DTA114TE

■ Features

- PNP Epitaxial Planar Silicon Transistor (Resistor Built-In Typ.)
- Built-In Bias Resistors Enable The Configuration of An Inverter Circuit Without Connecting External Input Resistors
(See Equivalent Circuit).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

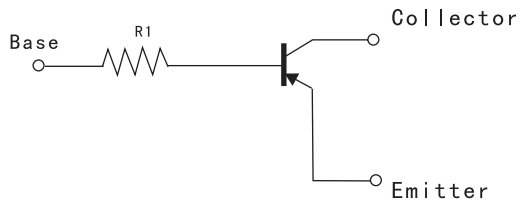
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _C = -50 μA	-50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA	-50			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -50 μA	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} = -50V			-0.5	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -4V			-0.5	μA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -10mA , I _B = -1mA			-0.3	V
DC Current Transfer Ratio	h _{FE}	V _{CE} = -5V , I _C = -1mA	100	250	600	
Input Resistance	R _I		7	10	13	kΩ
Transistion Frequency	f _T *	V _{CE} = -10V , I _E = 5mA , f = 100MHz		250		MHZ

* Characteristics of built-in transistor

■ Marking

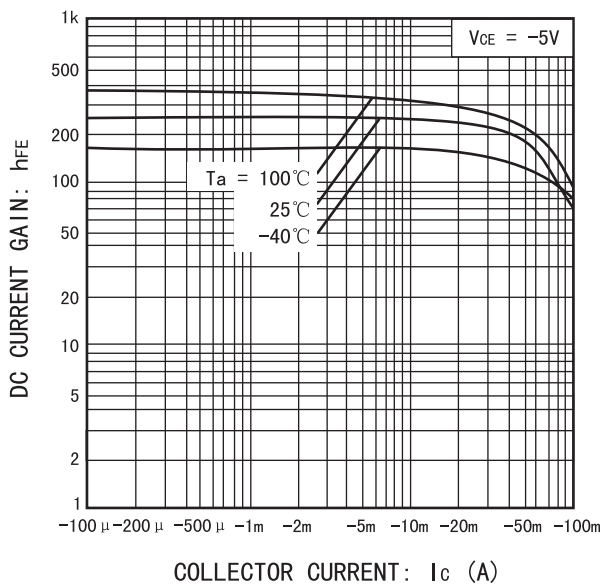
Marking	94
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■ Equivalent Circuit

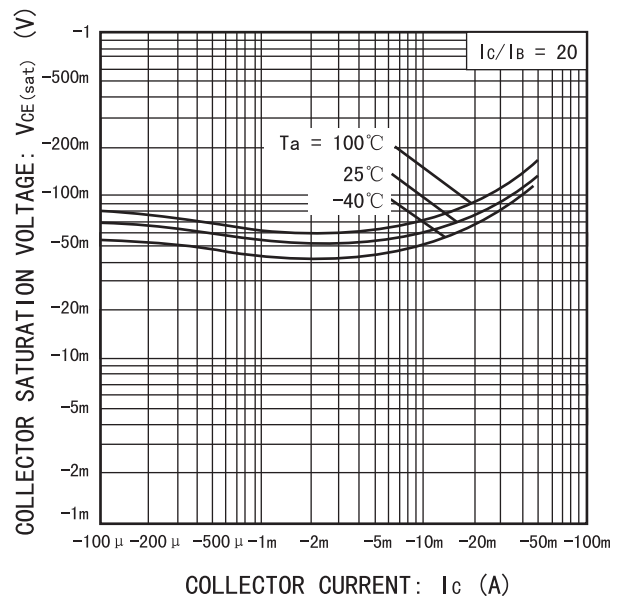


$R_1 = 10k\Omega$

■ Electrical Characteristics Curves



DC current gain vs. collector current



Collector-emitter saturation voltage vs. collector current